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8/7/06 JSR

IN THE SPECIFICATION:

Please amend the abstract as follows:

ABSTRACT

[0027] Disclosed is a method for forming an optical mask that has reduced processing steps. The invention performs a first patterning of an opaque chrome layer to expose a first region of the transparent quartz substrate and then etches the first region of the transparent quartz substrate through the chrome layer to create a phase shift region within the transparent quartz substrate. Next, the invention performs additional patterning of the opaque chrome layer to expose a second region of the transparent quartz substrate that is adjacent to the first region. This additional patterning process enlarges the opening formed in the opaque mask formed in the first patterning process. The first region and the second region comprise a continuous area of the transparent quartz substrate.

Please amend paragraphs 0006, 0007, 0019, and 0023 as follows:

[0006] The process here is beneficial because it eliminates levels of processing, as well as reduces the complexity of processing. The fact that less lithography levels are required immediately reduces the number of design levels (design complexity, data volume, etc.). Reduction in lithography levels also reduces the process complexity, and length (i.e., better yields, and turn around time (TAT)). With the invention, the overlay requirements for each level also become less stringent, which improves yield, and TAT.

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